

# ST - 23G

The ST - 23G, a high - sensitivity NPN silicon phototransistor mounted in a clear sidelooking package, is compact, low profile and easy to mount.

### FEATURES

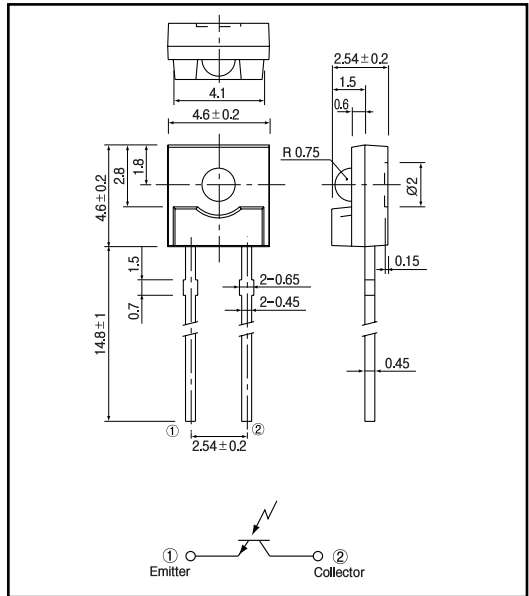
- Low profile package
- Compact
- Low - cost
- Sidelooking plastic package

### APPLICATIONS

- Photointerrupters
- Optical switches

### DIMENSIONS

(Unit : mm)



### MAXIMUM RATINGS

(Ta=25 )

Item	Symbol	Rating	Unit
C - E voltage	V <sub>CEO</sub>	30	V
E - C voltage	V <sub>ECO</sub>	6	V
Collector current	I <sub>c</sub>	40	mA
Collector power dissipation	P <sub>c</sub>	100	mW
Operating temp.	T <sub>opr.</sub>	- 20 ~ + 100	
Storage Temp.	T <sub>stg.</sub>	- 30 ~ + 100	
Soldering temp. *1	T <sub>sol.</sub>	260	

\*1. For MAX.5 seconds at the position of 2 mm from the package

### ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25 )

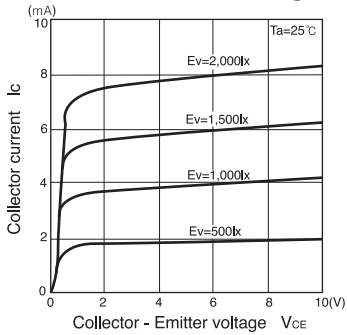
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Collector dark current	I <sub>CEO</sub>	V <sub>CEO</sub> = 10V		1	100	nA
Light current	I <sub>L</sub>	V <sub>CE</sub> = 5V, 1,000lx <sup>-2</sup>	0.5	4.0	20	mA
C - E saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 0.5mA, 2,000lx <sup>-2</sup>		0.2	0.4	V
Switching speeds	Rise time	V <sub>CC</sub> = 10V, I <sub>c</sub> = 5mA, R <sub>L</sub> = 100		3.2		µsec.
	Fall time			4.8		µsec.
Spectral sensitivity				500 - 1,050		nm
Peak wavelength	p			880		nm
Half angle				± 30		deg.

\*2. Color temp. = 2856K standard Tungsten lamp

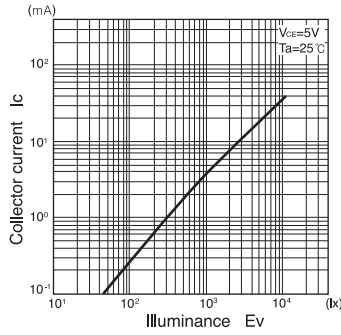
Photo transistors

ST - 23G

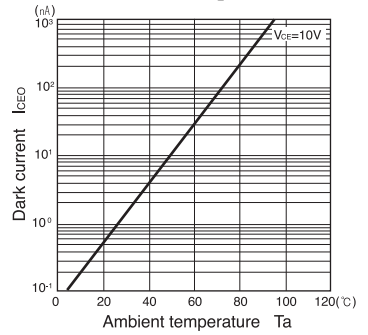
**Collector current Vs. Collector - Emitter voltage**



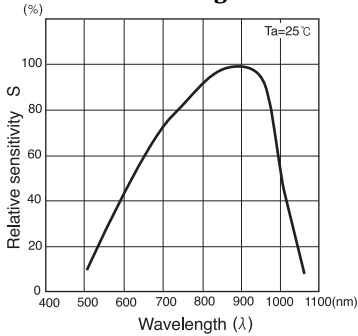
**Collector current Vs. Illuminance**



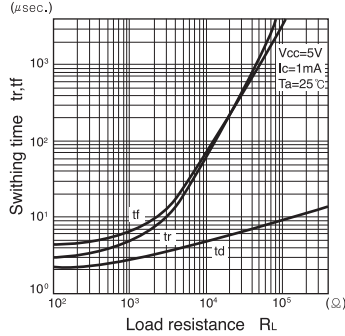
**Dark current Vs. Ambient temperature**



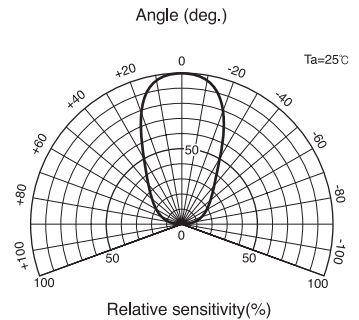
**Relative sensitivity Vs. Wavelength**



**Switching time vs. Load resistance**



**Radiant Pattern**



**Collector power dissipation Vs. Ambient temperature**

